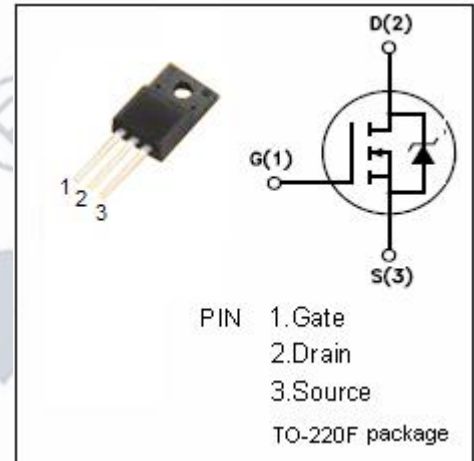


**isc N-Channel Mosfet Transistor****HG2N60****• FEATURES**

- Drain Current  $-I_D = 2A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 4.5 \Omega (\text{Max})$
- Avalanche Energy Specified
- Fast Switching
- Simple Drive Requirements

**• DESCRIPTION**

- High efficiency switch mode power supply.  
Charger  
UPS power supply.

**• ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 30$	V
$I_D$	Drain Current-Continuous	2	A
$I_{DM}$	Drain Current-Single Pulsed	6	A
$P_D$	Total Dissipation @ $T_C = 25^\circ C$	50	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$

**isc N-Channel Mosfet Transistor****HG2N60****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$ ; $I_D=0.25\text{mA}$	600		V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ ; $I_D=0.25\text{mA}$	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$ ; $I_D=1\text{A}$		4.5	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}$ ; $V_{DS}=0$		$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=600\text{V}$ ; $V_{GS}=0$		5	$\mu\text{A}$
$V_{SD}$	Forward On-Voltage	$I_S=2\text{A}$ ; $V_{GS}=0$		1.4	V